

Features

- High current TRIAC
- Low thermal resistance with clip bonding
- High commutation capability
- Packages are RoHS (2011/65/EU) compliant

Applications

- On/off function in static relays, heating regulation, induction motor starting circuits
- Phase control operations in light dimmers, motor speed controllers, and similar

Description

Available in high power packages, the BTA/BTB40-41 series is suitable for general purpose AC switching.

The BTA series provides an insulated tab (rated at 3500 V rms).

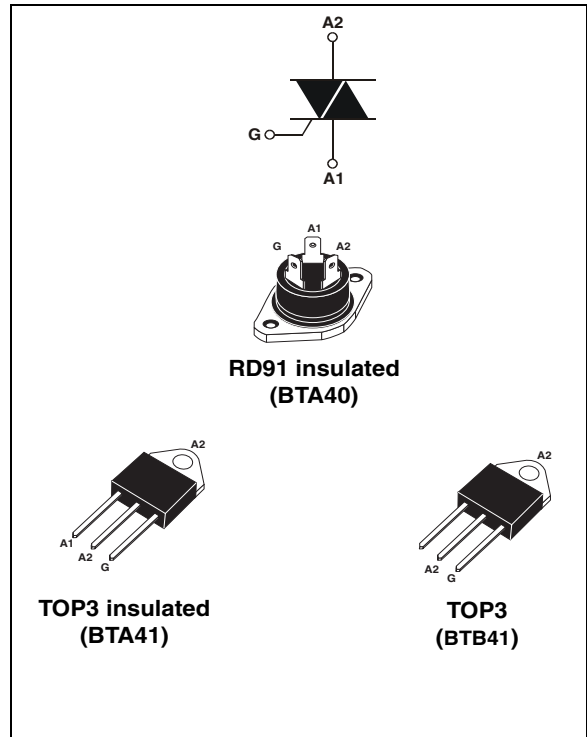


Figure 1. Ordering information scheme

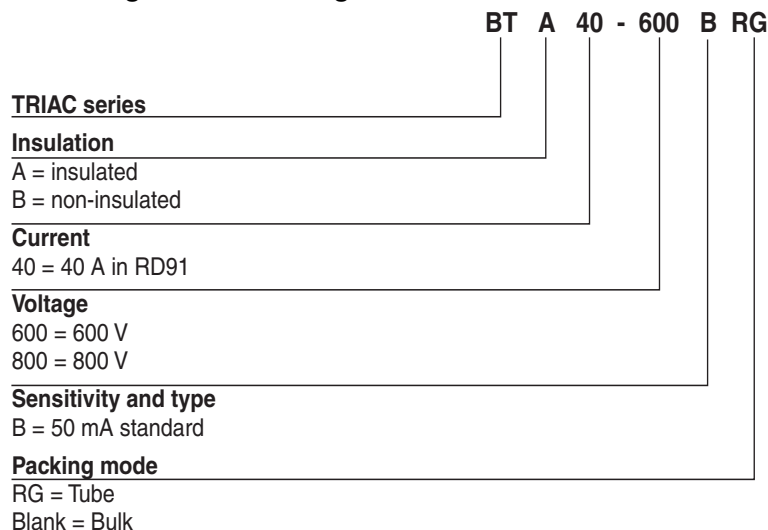


Table 1. Device summary

Symbol	Parameter	BTA40 ⁽¹⁾	BTA41 ⁽¹⁾	BTB41	Unit
$I_{T(RMS)}$	On-state rms current	40	41	41	A
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage	600 and 800	600 and 800	600 and 800	V
I_{GT}	Triggering gate current	50	50	50	mA

1. Insulated package

1 Characteristics

Table 2. Absolute maximum ratings

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	On-state rms current (full sine wave)	TOP3	$T_c = 95\text{ }^\circ\text{C}$	40	A
		RD91 / TOP ins.	$T_c = 80\text{ }^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial = $25\text{ }^\circ\text{C}$)	F = 50 Hz	t = 20 ms	400	A
		F = 60 Hz	t = 16.7 ms	420	
I^2t	I^2t Value for fusing	$t_p = 10\text{ ms}$		1000	A^2s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100\text{ ns}$	F = 120 Hz	$T_j = 125\text{ }^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
V_{DSM}/V_{RSM}	Non repetitive surge peak off-state voltage	$t_p = 10\text{ ms}$	$T_j = 25\text{ }^\circ\text{C}$	$V_{DSM}/V_{RSM} + 100$	V
I_{GM}	Peak gate current	$t_p = 20\text{ }\mu\text{s}$	$T_j = 125\text{ }^\circ\text{C}$	8	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125\text{ }^\circ\text{C}$	1	W
T_{stg} T_j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	$^\circ\text{C}$

Table 3. Electrical characteristics ($T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter			Value	Unit
$I_{GT}^{(1)}$	$V_D = 12\text{ V}$ $R_L = 33\text{ }\Omega$	I - II - III	MAX.	50	mA
		IV		100	
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{ k}\Omega$ $T_j = 125\text{ }^\circ\text{C}$	ALL	MIN.	0.2	V
$I_H^{(2)}$	$I_T = 500\text{ mA}$		MAX.	80	mA
I_L	$I_G = 1.2 I_{GT}$	I - III - IV	MAX.	70	mA
		II		160	
$dV/dt^{(2)}$	$V_D = 67\% V_{DRM}$ gate open	$T_j = 125\text{ }^\circ\text{C}$	MIN.	500	$\text{V}/\mu\text{s}$
$(dV/dt)_c^{(2)}$	$(dl/dt)_c = 20\text{ A/ms}$	$T_j = 125\text{ }^\circ\text{C}$	MIN.	10	$\text{V}/\mu\text{s}$

1. Minimum I_{GT} is guaranteed at 5% of I_{GT} max.
2. for both polarities of A2 referenced to A1

Table 4. Static characteristics

Symbol	Test conditions		Value	Unit		
$V_T^{(1)}$	$I_{TM} = 60\text{ A}$	$t_p = 380\ \mu\text{s}$	$T_j = 25\ ^\circ\text{C}$	MAX.	1.55	V
$V_{T0}^{(2)}$	Threshold voltage		$T_j = 125\ ^\circ\text{C}$	MAX.	0.85	V
$R_d^{(2)}$	Dynamic resistance		$T_j = 125\ ^\circ\text{C}$	MAX.	10	m Ω
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM}$		$T_j = 25\ ^\circ\text{C}$	MAX.	5	μA
			$T_j = 125\ ^\circ\text{C}$		5	mA

1. Minimum I_{GT} is guaranteed at 5% of I_{GT} max.
2. for both polarities of A2 referenced to A1

Table 5. Thermal resistance

Symbol	Test conditions		Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	RD91 (insulated) / TOP3 insulated	0.9	$^\circ\text{C/W}$
		TOP3	0.6	
$R_{th(j-a)}$	Junction to ambient	TOP3 / TOP3 insulated	50	$^\circ\text{C/W}$

Figure2. Maximum power dissipation versus on-state rms current (full cycle)

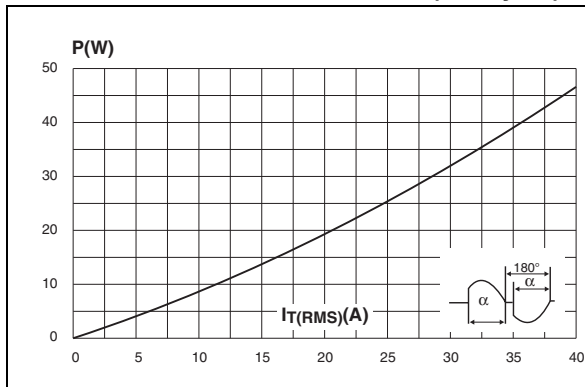


Figure3. On-state rms current versus case temperature (full cycle)

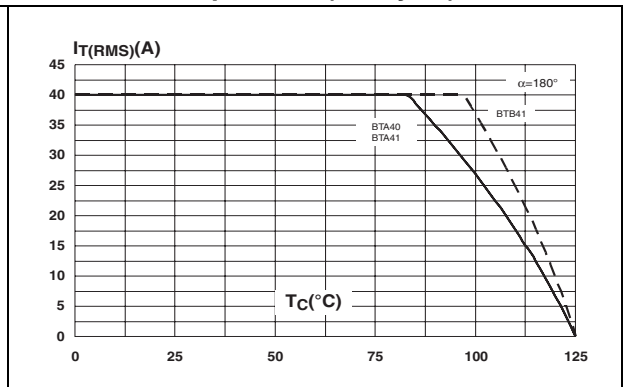


Figure4. Relative variation of thermal impedance versus pulse duration

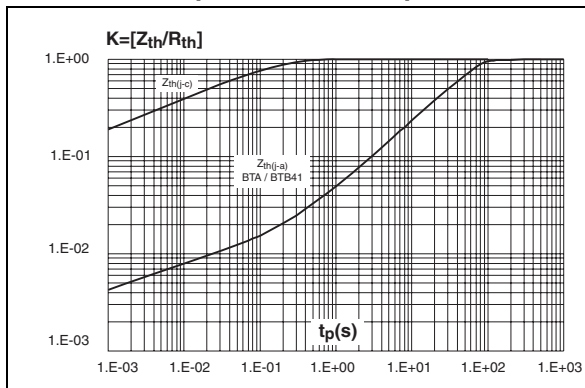


Figure5. On-state characteristics (maximum values)

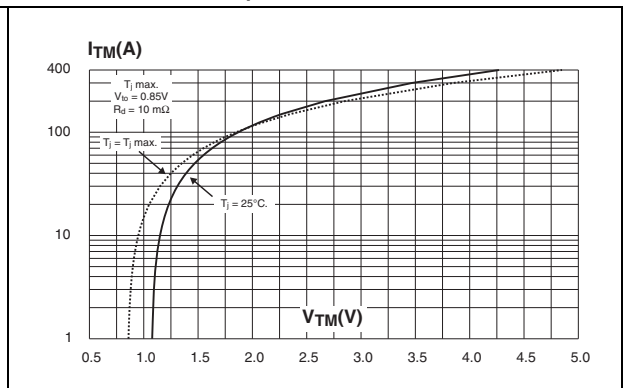


Figure 6. Surge peak on-state current versus number of cycles

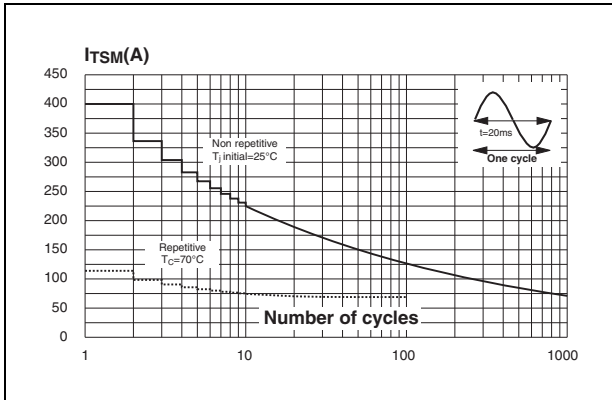


Figure 7. Non-repetitive surge peak on-state current for a sinusoidal pulse and corresponding value of I^2t

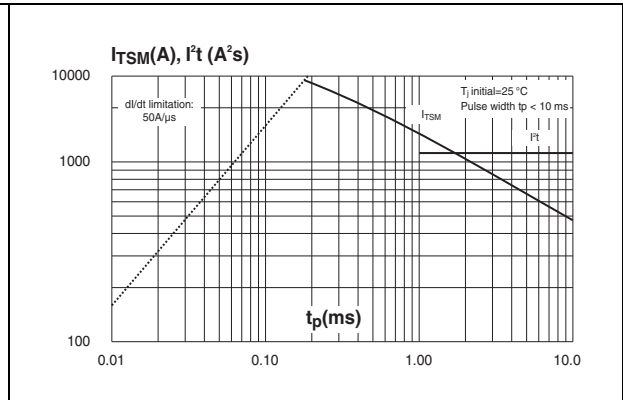


Figure 8. Relative variation of gate trigger, holding and latching current versus junction temperature

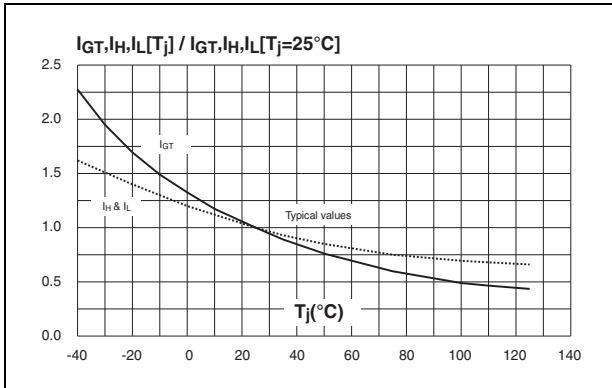


Figure 9. Relative variation of critical rate of decrease of main current versus $(dV/dt)c$ (typical values)

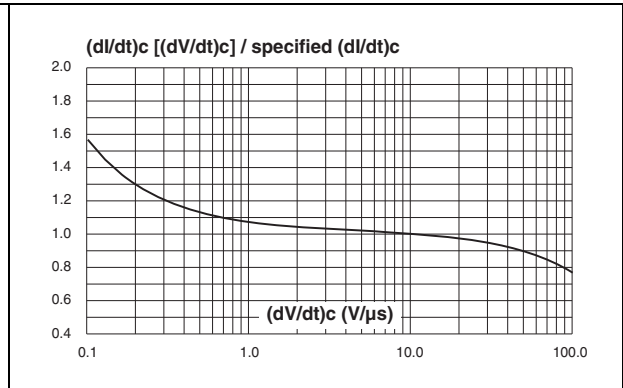


Figure 10. Relative variation of critical rate of decrease of main current versus $(dV/dt)c$

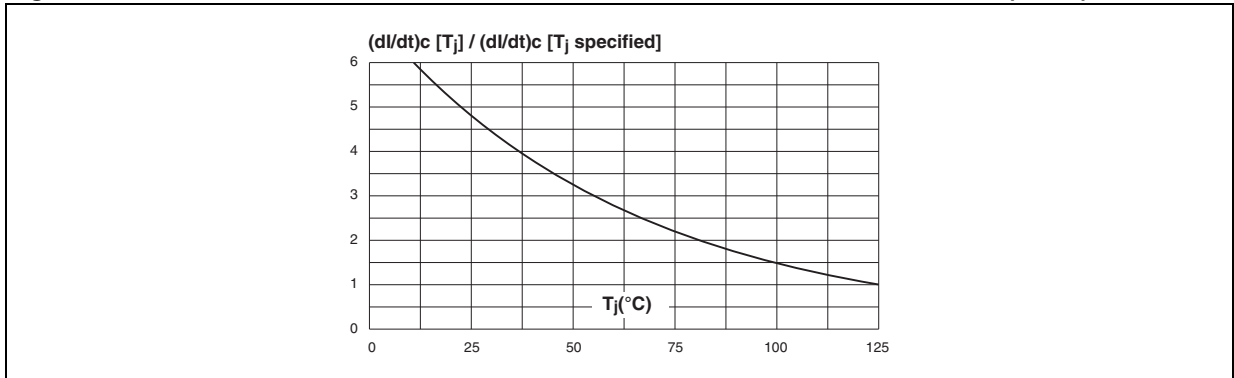


Table 6. TOP3 insulated and non-insulated dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	1.45	1.55	0.057	0.061
C	14.35	15.60	0.565	0.614
D	0.5	0.7	0.020	0.028
E	2.7	2.9	0.106	0.114
F	15.8	16.5	0.622	0.650
G	20.4	21.1	0.815	0.831
H	15.1	15.5	0.594	0.610
J	5.4	5.65	0.213	0.222
K	3.4	3.65	0.134	0.144
ØL	4.08	4.17	0.161	0.164
P	1.20	1.40	0.047	0.055
R	4.60 typ.		0.181 typ.	

Table 7. RD91 dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	-	40.00	-	1.575
A1	29.90	30.30	1.177	1.193
A2	-	22.00	-	0.867
B	-	27.00	-	1.063
B1	13.50	16.50	0.531	0.650
B2	-	24.00	-	0.945
C	-	14.00	-	0.551
C1	-	3.50	-	0.138
C2	1.95	3.00	0.077	0.118
E3	0.70	0.90	0.027	0.035
F	4.00	4.50	0.157	0.177
I	11.20	13.60	0.441	0.535
L1	3.10	3.50	0.122	0.138
L2	1.70	1.90	0.067	0.075
N1	33°	43°	33°	43°
N2	28°	38°	28°	38°

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